PBSS4112PAN

120 V, 1 A NPN/NPN low VCEsat (BISS) transistor

Product data sheet

1. Product profile

1.1 General description

NPN/NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package. NPN/PNP complement: PBSS4112PANP. PNP/PNP complement: PBSS5112PAP.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- · Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

1.3 Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	Per transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	120	V
I _C	collector current			-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	1.5	Α
Per transisto	7						
R _{CEsat}	collector-emitter saturation resistance	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C		-	-	240	mΩ



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	Transparent top view Sym140 DFN2020-6 (SOT1118) E1 B1 C2 Sym140	E1 B1 C2
6	C1	collector TR1		sym140
7	C1	collector TR1	DI 112020-3 (0011110)	
8	C2	collector TR2		

Ordering information

Table 3. **Ordering information**

Type number	Package			
	Name	Description	Version	
PBSS4112PAN	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118	

Marking 4.

Table 4. **Marking codes**

Type number	Marking code
PBSS4112PAN	2R

Limiting values 5.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

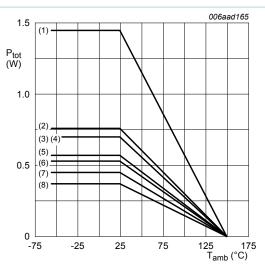
Symbol	Parameter	Conditions		Min	Max	Unit		
Per transist	Per transistor							
V_{CBO}	collector-base voltage	open emitter		-	120	V		
V_{CEO}	collector-emitter voltage	open base		-	120	V		
V _{EBO}	emitter-base voltage	open collector		-	7	V		
I _C	collector current			-	1	Α		
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1.5	Α		
I _B	base current			-	0.3	Α		
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Symbol	Parameter	Conditions		Min	Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			<u>[5]</u>	-	450	mW
			<u>[6]</u>	-	760	mW
			[7]	-	700	mW
			[8]	-	1450	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
			[8]	-	2000	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- 2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- 6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

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- (1) 4-layer PCB 70 μm, mounting pad for collector 1 cm²
- (2) FR4 PCB 70 µm, mounting pad for collector 1 cm²
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm²
- (5) FR4 PCB 35 μm, mounting pad for collector 1 cm²
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transist	Per transistor							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	338	K/W	
	from junction to ambient		[2]	-	-	219	K/W	
ambient		[3]	-	-	236	K/W		
		1	[4]	-	-	179	K/W	
			[5]	-	-	278	K/W	
			[6]	-	-	164	K/W	
			[7]	-	-	179	K/W	
			[8]	-	-	86	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W	

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device			'				
R _{th(j-a)}	thermal resistance in free air	[1]	-	-	245	K/W	
		ambient	[2]	-	-	160	K/W
	ambient		[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
		[6]	-	-	120	K/W	
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

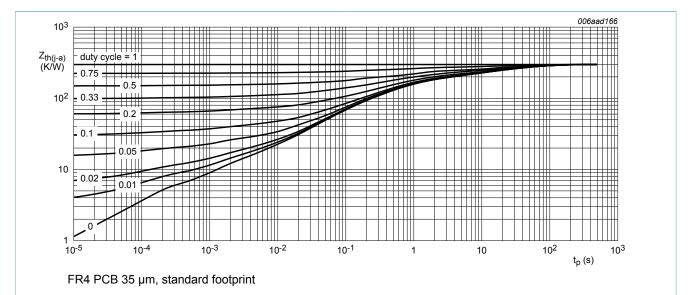
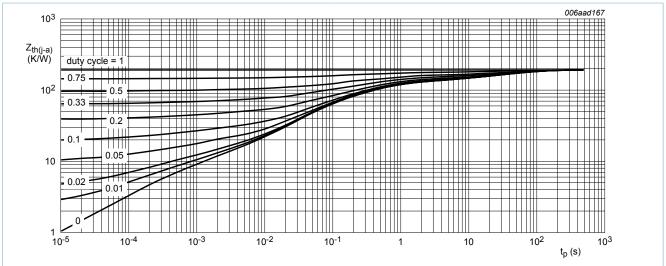


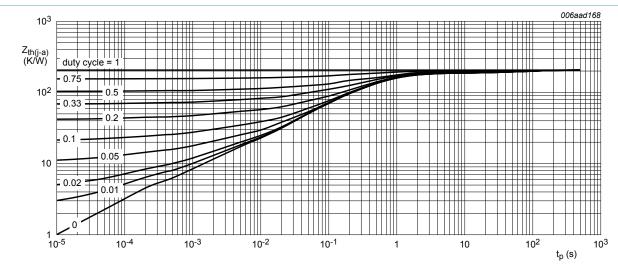
Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB 35 µm, mounting pad for collector 1 cm²

Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 35 µm, standard footprint

Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

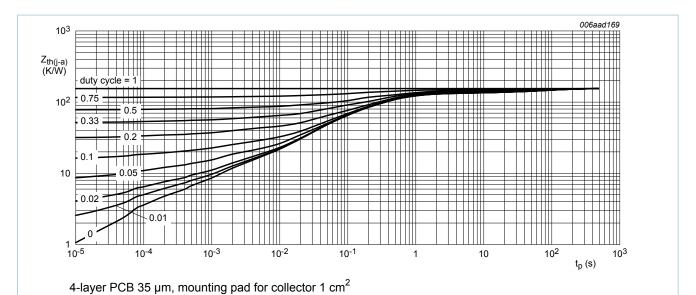


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

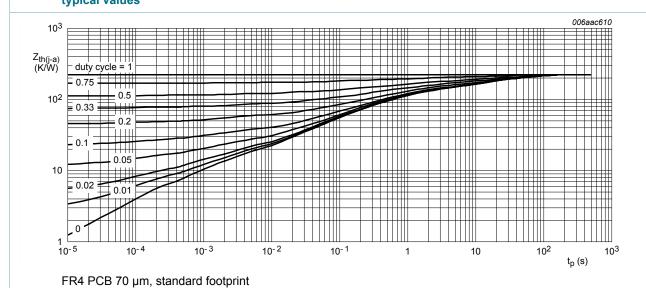


Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

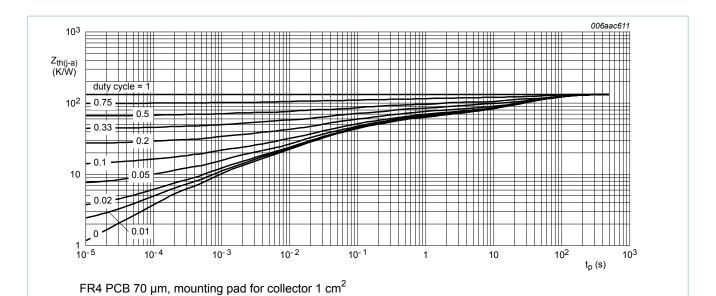


Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

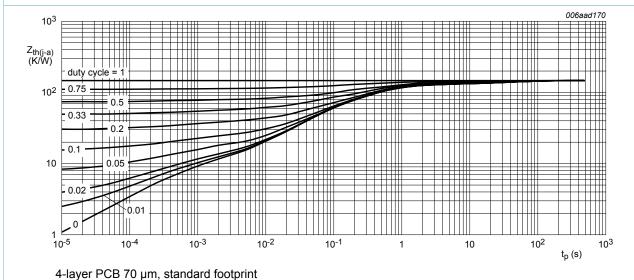


Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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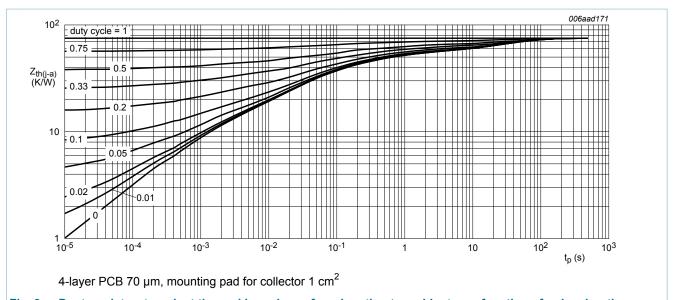


Fig. 9. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

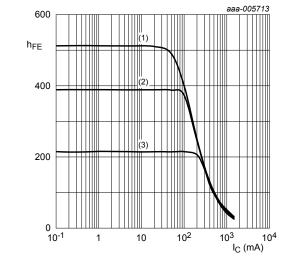
7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mii	т Тур	Max	Unit		
Per transisto	Per transistor							
I _{CBO}	collector-base cut-off	V _{CB} = 96 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA		
	current	V _{CB} = 96 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA		
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA		
h _{FE} DC current gain		V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	24	0 375	-			
		V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	60	100	-			
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	30	45	-			
V _{CEsat}	collector-emitter	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	90	120	mV		
	saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	205	260	mV		
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	170	220	mV		
R _{CEsat}	collector-emitter saturation resistance	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	240	mΩ		

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}		I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	1	V
voltage	voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.1	V
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	0.9	V
t _d	delay time	V _{CC} = 10 V; I _C = 500 mA; I _{Bon} = 25 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -25 mA; T _{amb} = 25 °C	-	440	-	ns
t _{on}	turn-on time		-	460	-	ns
ts	storage time		-	615	-	ns
t _f	fall time		-	390	-	ns
t _{off}	turn-off time		-	1005	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	60	120	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	4.5	7	pF



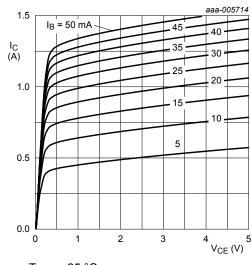
V_{CE} = 2 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

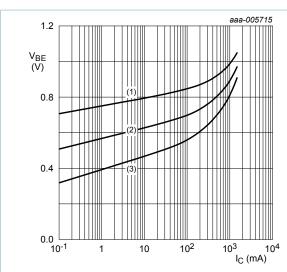
(3) $T_{amb} = -55$ °C

Fig. 10. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 11. Collector current as a function of collectoremitter voltage; typical values



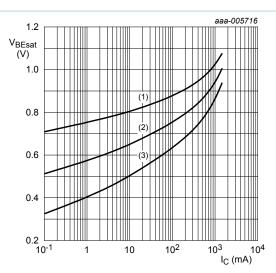
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$





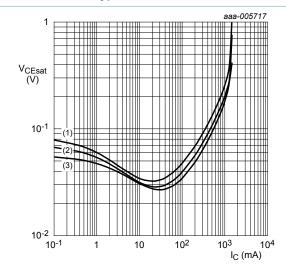
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. Base-emitter saturation voltage as a function of collector current; typical values



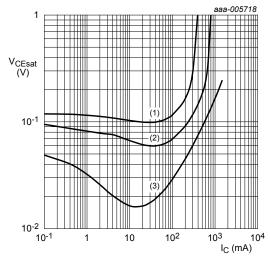
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

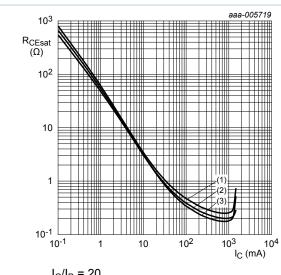


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values



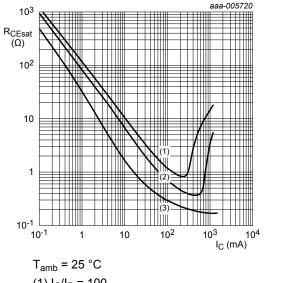
$$I_C/I_B = 20$$

(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

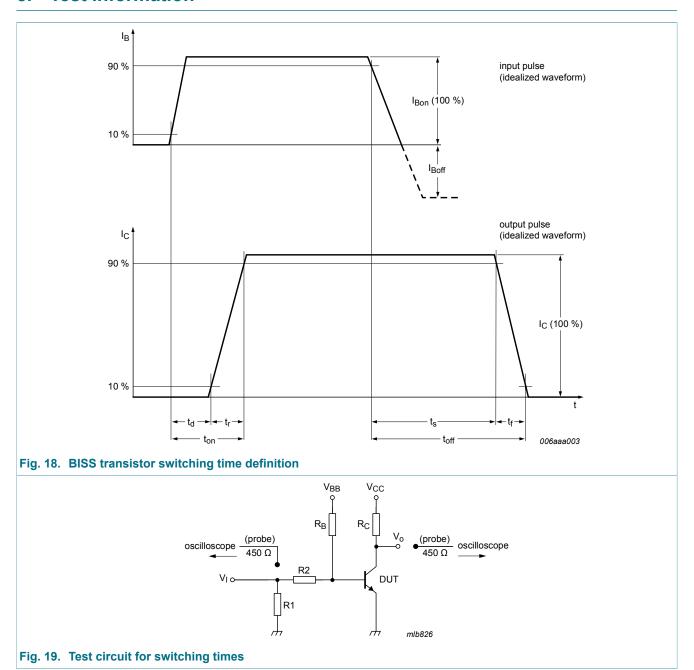
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

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8. Test information

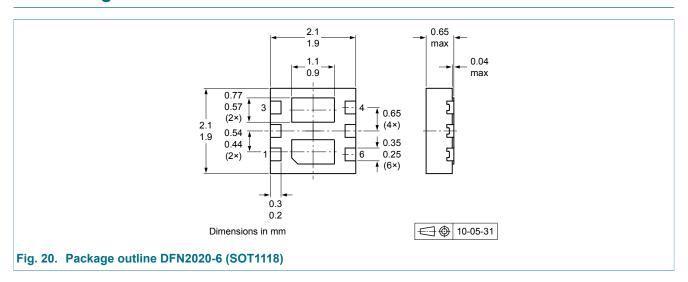


8.1 Quality information

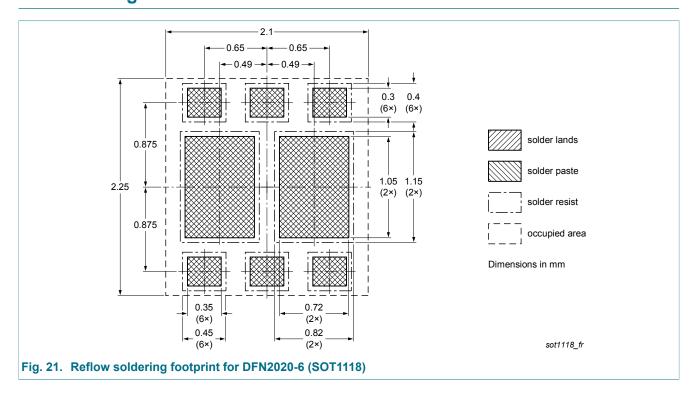
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Soldering



11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4112PAN v.N	20121129	Product data sheet	-	-		

PBSS4112PAN

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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